Investigating the high-temperature thermoelectric properties of n-type rutile TiO$_2$

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Transition metal oxides are considered promising thermoelectric materials for harvesting high-temperature waste heat due to their stability, abundance and low toxicity. Despite their typically strong ionic character, they can exhibit surprisingly high power factors $\sigma S^2$, as in n-type SrTiO$_3$ for instance. Thus, it is worth examining other transition metal oxides that might surpass the performances of SrTiO$_3$. This theoretical paper investigates the thermoelectric properties of n-type rutile TiO$_2$, which is the most stable phase of titanium oxide up to 2000 K. The electronic structure is obtained through ab initio calculations, while the prominent features of strong electron-phonon interaction and defects states are modelled using a small number of parameters. The theoretical results are compared with a wealth of experimental data from the literature, yielding very good agreements over a wide range of carrier concentrations. This validates the hypothesis of band conduction in rutile TiO$_2$ and allows the prediction of the high-temperature thermoelectric properties.

In the past decades, the global energy crisis has led to a renewed interest in the prospect of thermoelectric power generation.$^{1–3}$ The thermoelectric performance of a given compound is measured by the figure of merit $zT = \sigma S^2 T/\kappa$, where $\sigma$ is the electrical conductivity, $S$ is the Seebeck coefficient and $\kappa$ is the thermal conductivity. $\kappa$ is usually dominated by the phonon properties, while $\sigma S^2$, called the power factor (PF), is governed by electronic transport. Widespread industrial use of thermoelectric devices would require a figure of merit reaching 2 to 4, a great challenge for materials science.$^{4,5}$

Recently, transition metal oxides have prompted great interest as potential thermoelectric materials because of their abundance and stability.$^{6,7}$ Although they are usually strongly polar, some of them can exhibit surprisingly high power factors, such as SrTiO$_3$ for instance.$^8$ However, optimization of bulk SrTiO$_3$ by doping and nanostructuring has been unable so far to yield figures of merit exceeding 0.5. Therefore, it is worth studying other transition metal oxides that might equal or even surpass these performances. Another well-known oxide is TiO$_2$, whose rutile phase is particularly stable at high temperatures with a melting point around 2100 K, and can be reduced to introduce oxygen vacancies acting as electron donors.$^9$ Therefore, this compound would represent a very promising prospect for high-temperature applications if its thermoelectric properties could be optimized.$^{10}$

In this paper, we investigate the electron transport properties of n-type rutile TiO$_2$ by combining first-principle calculations with a modelling of electron-phonon interactions and donor defects, allowing us to directly compare our results with reported thermoelectric measurements. TiO$_2$ being a very polar material, strong interactions between electrons and optical phonons in rutile give rise to intrinsic small polarons at low temperature, i.e. the electrons are self-trapped by the surrounding lattice deformation. This has been observed both experimentally$^{11}$ and in Density Functional Theory (DFT) calculations using hybrid functionals$^{12}$ or DFT+U methodology.$^{13}$ On the other hand, the small polarons have been found highly unstable at room-temperature, as well as only slightly favoured energetically compared to delocalized conduction states, with an energy barrier hindering the localization of extended electrons.$^{14,15}$ Furthermore, the mobility predicted by the small polaron hopping mechanism is orders of magnitudes lower than the experimental estimates in reduced samples.$^{16}$ The measured mobility above 100 K also decreases when the temperature is elevated,$^{17}$ suggesting conduction band transport. Therefore, it is likely that the transport properties at room-temperature and above are dominated by delocalized electrons in the conduction band. For these reasons, we will investigate the thermoelectric properties of rutile TiO$_2$ assuming delocalized conduction electrons. Although standard Generalized Gradient Approximation (GGA) functionals are unable to describe small polarons, they predict the same conduction band structure as hybrid functionals that have been used to investigate them.$^{18}$ Therefore, we will compute the band structure using the GGA, and we will introduce parameters to model the electron scattering and mass renormalization that are expected to result from strong electron-phonon coupling. They will be set by direct comparison with experimental measurements.

We show in Fig 1 the crystal structure of rutile TiO$_2$, as well as the electron dispersion and the density of states (DOS) of the conduction band, computed using the DFT package SIESTA$^{19}$ (details are given in the supplementary material). The black lines correspond to the SIESTA results, and the cyan lines and the DOS are calculated from Wannier projections of the Bloch states onto the 3d orbitals of the Ti atoms, using the Wannier90 software.$^{20}$ The band structures predicted by the two methods are in excellent agreement. The conduction band effective mass in the $z$ direction is $m^*_{e} = 0.63 m_e$, while the effective masses in the $x$ and $y$ directions are $m^*_{e} = m^*_{b} = 1.3 m_e$. There is some anisotropy, but much less than in SrTiO$_3$ in which the ratio of the effective masses is as high as 10.

The electrical conductivity $\sigma$ and the Seebeck coefficient $S$ of n-type rutile TiO$_2$ are calculated within the framework of the Boltzmann transport equation (BTE) under the relaxation time approximation (RTA) (more
Figure 1: Top: the conventional cell of rutile TiO$_2$, where the grey and red spheres represent the Ti and O atoms respectively. Bottom: The band structure and density of states of the conduction band, from full DFT calculations (black lines) and from Wannier projections (cyan lines and DOS).

Figure 2: Left: the experimental (circles, Ref. 21) and theoretical scattering rate $\hbar/\tau$ in meV. The theoretical values correspond to the bottom of the conduction band at the $\Gamma$ point. Right: The experimental (circles, Ref. 17) and theoretical mobility $\mu$ in the $z$ direction, in cm$^2$ V$^{-1}$ s$^{-1}$.

details are given in the supplementary material). The relaxation time is taken to be the energy and temperature dependant electron lifetime $\tau(E,T)$. Since we are interested in high-temperature power generation, it is important to provide an accurate modelling of the lifetime including the correct temperature dependance. The scattering rate $\hbar/\tau$ has been measured in Ref. 21 from 11 K to 300 K. Although it increases with temperature, the dependance between 100 K and 300 K is inconsistent with the typical $3/2$ power-law of the acoustic deformation potential mechanism. On the other hand, the large interaction between electrons and optical phonons can be expected to dominate scattering in such a polar compound, provided that the optical modes are sufficiently populated. The phonon spectrum in rutile TiO$_2$ features optical modes from 15 meV to 100 meV. Thus, longitudinal optical (LO) modes should be populated at 300 K and above, leading to a significant polar-optical scattering rate. Assuming a parabolic dispersion for the conduction band electrons and a flat one for the LO branches, second order perturbation theory gives

$$
\frac{\hbar}{\tau(E,T)} = 2\alpha \sqrt{E} \sum_\nu (\hbar \omega_\nu)^{\frac{3}{2}} \left[ N_\nu \text{Arsh} \left( \frac{E}{\hbar \omega_\nu} \right) + \Theta(E - \hbar \omega_\nu) (N_\nu + 1) \text{Arsh} \left( \frac{E}{\hbar \omega_\nu} - 1 \right) \right],
$$

where $\Theta$ is the Heaviside function, $\alpha$ is the Fröhlich coupling constant, $\nu$ is an index running over the LO branches, $\omega_\nu$ is the $\Gamma$-point frequency of the branch $\nu$ and $N_\nu = 1/(e^{\beta \hbar \omega_\nu} - 1)$ is the Bose-Einstein distribution (see the supplementary material for more details on $\hbar/\tau$). We have assumed $\alpha$ to be the same for all modes. To set the value of this single parameter, we compare the calculated scattering rate at the $\Gamma$ point with the experimental values between 100 K and 300 K. As shown in Fig. 2 (left panel), the choice $\alpha = 0.85$ leads to a good agreement between theory and experiment, thus validating our assumption of dominant polar-optical electron scattering. This value corresponds to a weak Fröhlich interaction with each phonon mode, consistent with the use of second order perturbation theory.

Having successfully modeled the temperature-dependant scattering rate, we now endeavour to reproduce the experimental mobilities $\mu = \sigma/ne$ (with $n$ the electron density) that have been measured in Ref. 17 for the $z$ direction. However, if we calculate the TDF from the $ab$ initio band-structure shown in Fig. 1, the predicted mobility is an order of magnitude higher than the measurements, indicating a large transport mass renormalization of the delocalized carriers due to electron-phonon interactions. This could seem surprising given the relatively low coupling constant $\alpha = 0.85$, but the conduction electrons in rutile TiO$_2$ interact with five different LO branches: in such cases, the effective coupling constant $\alpha_{\text{eff}}$ for a one-branch interaction is given by $\alpha_{\text{eff}} = \sum_\nu \alpha_\nu$. This gives $\alpha_{\text{eff}} = 4.25$ corresponding to intermediate-strong coupling, consistent with small polarons that are slightly favoured energetically and a large mass renormalization of the delocalized conduction electrons. It is then natural to wonder why the perturbative expression for the scattering rate is validated by experiments, given the strong value of the overall electron-phonon coupling constant. It must be kept in mind that, for delocalized electrons close to a metal-insulator transition, the single-particle properties (i.e. the band mass and the
scattering rate obtained from the spectral function) may not be critical quantities. However, the transport mass associated with the conductivity can be much more sensitive and may be considerably enhanced due to so-called vertex corrections. This scenario resolves the apparent contradiction between a large mass renormalization and the delocalized behaviour exhibited by electrons in rutile TiO$_2$. To take this effect into account in the simplest way, we introduce the renormalization parameters $f_z$ and $f_x = f_y$ for transport in the $z$ and $xy$ directions, respectively. Only the TDF is renormalized: $\Sigma_i(E, T) \rightarrow \Sigma_i(E, T)/f_i$, and the electron mobilities are calculated to be compared with experiment. As shown in Fig. 2 (right panel), the large value $f_z = 7$ leads to an excellent agreement. The $xy$ factor is even larger: $f_x = 23.5$, comparable to the effective masses found in Ref. 17 by fitting the transport measurements.

The transport properties can then be calculated as functions of the electron density $n$, and compared with experimental data. We show in Fig. 3 (left panel) the room-temperature electrical conductivity in the $z$ direction (red), in the $xy$ directions (green) and in polycrystalline materials (orange) for which an orientational average was taken. Experimental data from Ref. 17,28–30 are also plotted. The agreement between theory and experiment is very good over a wide range of carrier concentration (five orders of magnitude). In the right panel of Fig. 3 is shown the predicted Seebeck coefficient as a function of the conductivity, together with experimental data from Ref. 9,28–31. Although the theory may somewhat underestimate the Seebeck coefficient in some samples, overall it agrees well with experiments. This success of the theory at 300 K supports the band conduction mechanism as opposed to small polaron hopping. Moreover, renormalizing the DOS by the parameters $f_z$ and $f_x$ would lead to a large discrepancy between the predicted and measured Seebeck coefficients, due to the Fermi level being pushed further in the gap. This is consistent with a renormalization of the transport mass only and a perturbative treatment of the one-particle properties.

As high-temperature generation is the main application prospect for TiO$_2$ as a thermoelectric material, it is crucial to accurately predict the transport properties between 300 K and 2000 K. In Ref. 9, the electrical conductivity and Seebeck coefficients of reduced rutile samples have been measured up to 523 K. The conductivity displays a very weak temperature dependence, even though the scattering rate increases substantially with elevated temperature. This suggests an activation mechanism for the electron density in the conduction band, as confirmed by the Hall measurements in Ref. 17 that clearly show an increase of the carrier density with temperature. On the theoretical side, several first-principle calculations of oxygen vacancies in rutile TiO$_2$ find energetically favored electronic bound states localized on neighboring Ti atoms.12,13,15,32,33 There is no consensus on the binding energy, although most experimental and theoretical estimates fall between 50 meV and 200 meV.

To capture the effects of this activation mechanism in a simple and general way, we model the presence of oxygen vacancies by adding localized defect levels inside the gap at an energy $\epsilon$. Thus, TiO$_2$-$\epsilon$ is modeled by adding a term $4\pi\delta(E-\epsilon)$ in the pristine DOS, while the TDF is unchanged (the impurity states have zero conductivity). The total carrier density is set at $4\pi$ electron/cell (each oxygen vacancy is assumed to bring 2 electrons), leading to an activation mechanism with more carriers populating the conduction band as temperature is increased. We adjust the parameters $\epsilon$ and $x$ to reproduce the experimental conductivities from the samples in Ref. 9 subjected to spark plasma sintering (SPS) at 1173 K, 1273 K and 1373 K. Fig. 4 shows the polycrystalline electrical conductivity, Seebeck coefficient and power factor for $\epsilon = -150$ meV and three vacancy concentrations $x = 1.3 \times 10^{-4}$, $x = 1.7 \times 10^{-3}$ and $x = 1.3 \times 10^{-2}$. These values lead to a rather good agreement with experimental data, and in particular they reproduce the weak temperature dependence of the transport properties, thus validating our approach. The shaded regions represent the sensibility of the results with respect to $\epsilon$, underscoring the satisfactory agreement between theory and experiment given the simplicity of the model. The important disparities in the predicted vacancy concentration between samples (two order of magnitudes) reflect similarly large variations in the measured resistivities.

The thermoelectric power factor $\sigma S^2$ of rutile TiO$_2$ can now be calculated between 300 K and 2000 K. Fig. 5 shows the predicted polycrystalline PF as a function of the density $n$ of conduction electrons for several temperatures (top) and as a function of temperature for several oxygen vacancy concentrations (bottom). The optimum carrier concentration is around 0.2 electron/cell, corre-
Figure 4: The predicted electrical conductivity (left), Seebeck coefficient (center), and power factor (right) of polycrystalline TiO$_{2-x}$ as a function of temperature for $x = 1.3 \times 10^{-4}$ (purple), $x = 1.7 \times 10^{-3}$ (red) and $x = 1.3 \times 10^{-2}$ (blue). The shaded regions correspond to a binding energy $\epsilon = -150 \pm 20$ meV. The circles are experimental data from Ref. 9.

Figure 5: Top: the polycrystalline power factor $\sigma S^2$ as a function of the density $n$ of conduction electrons for several temperatures. Inset: the maximum PF as a function of temperature. Bottom: the PF of polycrystalline TiO$_{2-x}$ as a function of temperature for several oxygen vacancy concentrations.

The maximum value of the figure of merit $zT_{\text{max}}$ can be roughly estimated assuming an amorphous value $\kappa \approx 1 \text{ W m}^{-1}\text{K}^{-1}$ for the thermal conductivity. This leads to $zT_{\text{max}} \approx 0.15$ around 1800 K. This value is six times lower than the estimate of Ref. 10, which aimed at comparing the different TiO$_2$ phases and thus did not include the temperature dependence of the scattering rate. Even accounting for the occasional underestimation of the predicted Seebeck coefficient, we do not expect the figure of merit to exceed 0.6. Therefore, if rutile TiO$_2$ is to be useful as a thermoelectric material, significant changes in its electronic structure must be engineered in order to boost the power factor beyond what can be reached by simply increasing the carrier concentration.

To conclude, we have investigated thermoelectric transport in n-type rutile TiO$_2$ through a combination of ab initio calculations and model descriptions of the electron-phonon interaction and oxygen vacancies. The parameters for the polar-optical scattering, mass renormalization and defect energy were set by comparisons between the predicted transport properties and available experimental data. A very good agreement between theory and experiment is obtained, supporting a band conduction picture of electronic transport. We predict a maximum power factor of $1.15 \mu\text{W cm}^{-1}\text{K}^{-2}$ leading to $zT \approx 0.15$ for an amorphous thermal conductivity. Therefore, the power factor must be boosted significantly before rutile TiO$_2$ can be widely used as a thermoelectric material. This might be achieved using quantum confinement and energy filtering effects, for instance.
Appendix A: *Ab initio* calculation of the electronic structure

We perform *ab initio* calculations with the DFT package SIESTA on the rutile structure of TiO$_2$. The standard Generalized Gradient Approximation (GGA) functional of Perdew, Burke, and Ernzerhof (PBE) and Troullier-Martins norm-conserving pseudopotentials are used. We perform an optimization of the double-$\zeta$-polarized basis with the Simplex tool of the SIESTA package. The unit cell is relaxed to forces less than 0.01 eV/Å and to a pressure less than 0.15 kbar. The self-consistent field cycles have been performed with a Monkhorst-Pack of $4 \times 4 \times 4$ k-points and a mesh cutoff of 400 Ry. We have checked that the band-structure predicted by the plane-wave based DFT package Quantum ESPRESSO is consistent with the results from SIESTA. In the Wannier basis, the Hamiltonian matrix elements with an amplitude lower than 1 meV have been cut. Since the experimental bandgap of rutile TiO$_2$ is rather large (more than 3 eV), a description of the valence band is unnecessary for the transport properties (we have checked that bipolar conduction is negligible in all our results).

![Wannier orbitals](image)

Figure 6: The Wannier orbitals associated with the conduction band of rutile TiO$_2$.

In Fig. 6 are shown the five Wannier orbitals centered on the central Ti atom of the TiO$_2$ unit cell, out of the ten orbitals that make up the conduction band of rutile TiO$_2$. They bear a strong resemblance with the 3d orbitals of the Ti atom, although there is significant weight on the 2p orbitals of the neighboring oxygens. They can be classified as low-energy $t_{2g}$-like orbitals and high-energy $e_g$-like orbitals following the crystal field classification. The partial density of states (PDOS) of the $t_{2g}$ and $e_g$ orbitals are shown in Fig. 7. Although the lower half of the conduction band is overwhelmingly composed of the $t_{2g}$ orbitals, there is still some weight from the $e_g$ ones at the bottom of the band, thus it is necessary to take the ten of them into account in order to properly describe the band-structure in the energy region of interest.

Appendix B: Calculation of the transport properties

We calculate the electron transport properties of n-type rutile TiO$_2$ within the framework of the Boltzmann transport equation (BTE), using the relaxation time approximation (RTA). The electrical conductivity and Seebeck coefficients in the $i$ direction ($i = x, y, z$) for a carrier concentration $n$ and a temperature $T$ are given by

$$\sigma_i(n, T) = \int dE \left( -\frac{\partial f}{\partial E} \right) \Sigma_i(E, T), \quad (B1)$$

and

$$S_i(n, T) = -\frac{1}{e T \sigma_i} \int dE \left( -\frac{\partial f}{\partial E} \right) (E - \mu_F) \Sigma_i(E, T), \quad (B2)$$

where $f(E, \mu_F, T)$ is the Fermi-Dirac distribution and the Fermi level $\mu_F$ is determined by integrating the DOS to find the correct electron concentration. $\Sigma_i(E, T)$ is called the transport distribution function (TDF), and its determination is key for the description of electron transport. Solving the BTE with the RTA gives

$$\Sigma_i(E, T) = \frac{2e^2}{\Omega} \sum_{\mathbf{k}, \lambda} v_{i, \mathbf{k}, \lambda}^2 \psi_{i, \mathbf{k}, \lambda}^\dagger \psi_{i, \mathbf{k}, \lambda} \delta(E - \epsilon_{i, \mathbf{k}, \lambda}), \quad (B3)$$

where $\Omega$ is the system size, $\mathbf{k}$ runs over the first Brillouin zone, $\lambda$ is the band index and the factor 2 accounts for spin degeneracy. $\epsilon_{i, \mathbf{k}, \lambda}$ is the energy of the eigenstate $(\mathbf{k}, \lambda)$, $v_{i, \mathbf{k}, \lambda}^i = \frac{\partial \epsilon_{i, \mathbf{k}, \lambda}}{\partial k_i}$ is the velocity in the $i$ direction, and $\tau_{i, \mathbf{k}, \lambda}$ is the lifetime, considered isotropic for simplicity.

The TDF is calculated using the Drude weight formalism. If the lifetime is a function of energy ($\tau_{i, \mathbf{k}, \lambda} = \tau(\epsilon_{i, \mathbf{k}, \lambda})$), the TDF in the $i$ direction can be written $\Sigma_i(E) = D_{0,i}(E) \tau(E)$ with

$$D_i(E) = \frac{2e^2}{\Omega} \sum_{\mathbf{k}, \lambda} v_{i, \mathbf{k}, \lambda}^2 \psi_{i, \mathbf{k}, \lambda}^\dagger \delta(E - \epsilon_{i, \mathbf{k}, \lambda}). \quad (B4)$$
\( D_i(E) \) is called the Drude weight. It can be re-expressed as

\[
D_i(E) = \frac{2e^2}{\hbar^2 \Omega} \sum_{\epsilon_{k,\lambda} < E} \frac{\partial^2 \epsilon_{k,\lambda}}{\partial k_i^2} = \frac{2}{\Omega} \sum \frac{\partial^2 \epsilon_{k,\lambda}}{\partial A_i^2}, \tag{B5}
\]

where \( A_i \) is a uniform vector potential in the \( i \) direction introduced through the Peierls substitution. We use the last expression in equation (B5) to calculate the Drude weight in practice.

In the parabolic approximation, the Drude weight reduces to \( D_i(E) = \frac{ne^2}{m_i} \), with \( n \) the carrier density. Thus, to take into account the mass enhancement due to electron-phonon interaction, we renormalize the Drude weight: \( D_i(E) \to \frac{D_i(E)}{f_i} \). The renormalized Drude weights in the \( xy \) directions, in the \( z \) direction and for polycrystalline samples (\( D_{\text{polycr}} = (2D_x + D_z)/3 \)) are shown in Fig. 8.

\[
\frac{\hbar}{\tau_{k,\lambda}} = \frac{2\alpha}{\sqrt{\epsilon_{k,\lambda}}} \sum_{\nu} (\hbar \omega_{\nu})^{\frac{3}{2}} \left[ N_{\nu} \text{Argsh} \left( \frac{\sqrt{\epsilon_{k,\lambda}}}{\hbar \omega_{\nu}} \right) \right] \tag{C1}
\]

where \( \Theta \) is the Heaviside function, \( \alpha \) is the Fröhlich coupling constant, \( \nu \) is a branch index running over the LO branches, \( \omega_{\nu} \) is the \( \Gamma \)-point frequency of the branch \( \nu \) and \( N_{\nu} = 1/(e^{\beta \hbar \omega_{\nu}} - 1) \) is the Bose-Einstein occupation factor. The first term inside the bracket corresponds to the absorption of an optical phonon, while the second term is associated with the emission of an optical phonon and thus requires the electron energy to be higher than the optical mode frequency. For simplicity, we have included all optical modes in the sum of equation (C1) and divided the result by 3. The optical mode frequencies, extracted from Ref. 24, are listed in Table I. The scattering rate as a function of energy is shown in Fig. 9a for several temperatures. The discontinuities in the derivative are caused by the absorption processes that activate when the energy reaches the phonon mode frequency. The scattering rate at the \( \Gamma \) point is shown in Fig. 9b as a function of temperature up to 2000 K. It becomes linear above 500 K as the optical modes are more and more populated.
Table I: The optical mode frequencies used in the calculation of the electron scattering rate.

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